



The Electron String Ion Sources (ESIS) cathode node electronics development

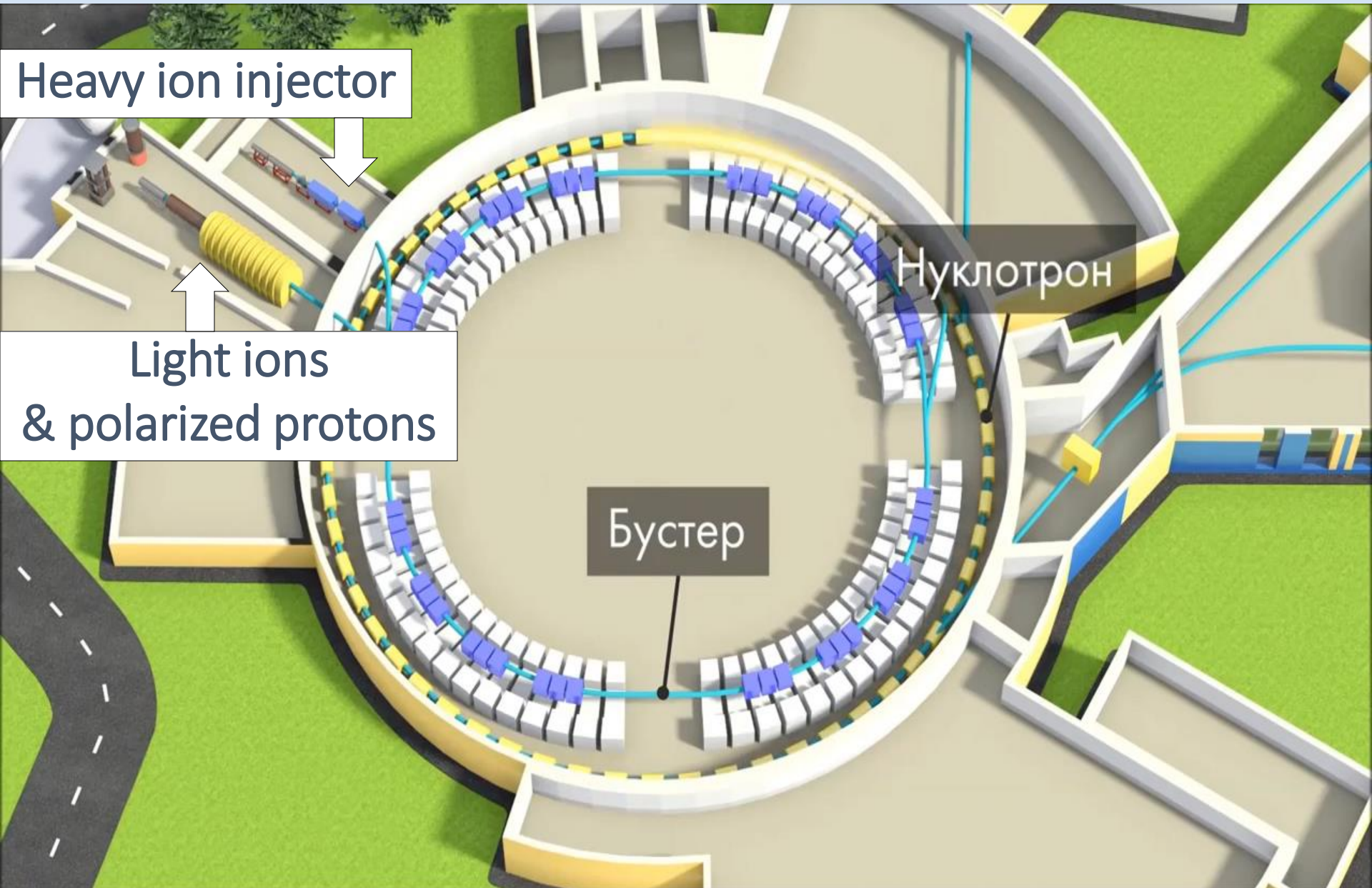
Ponkin Dmitry

LHEP JINR senior engineer

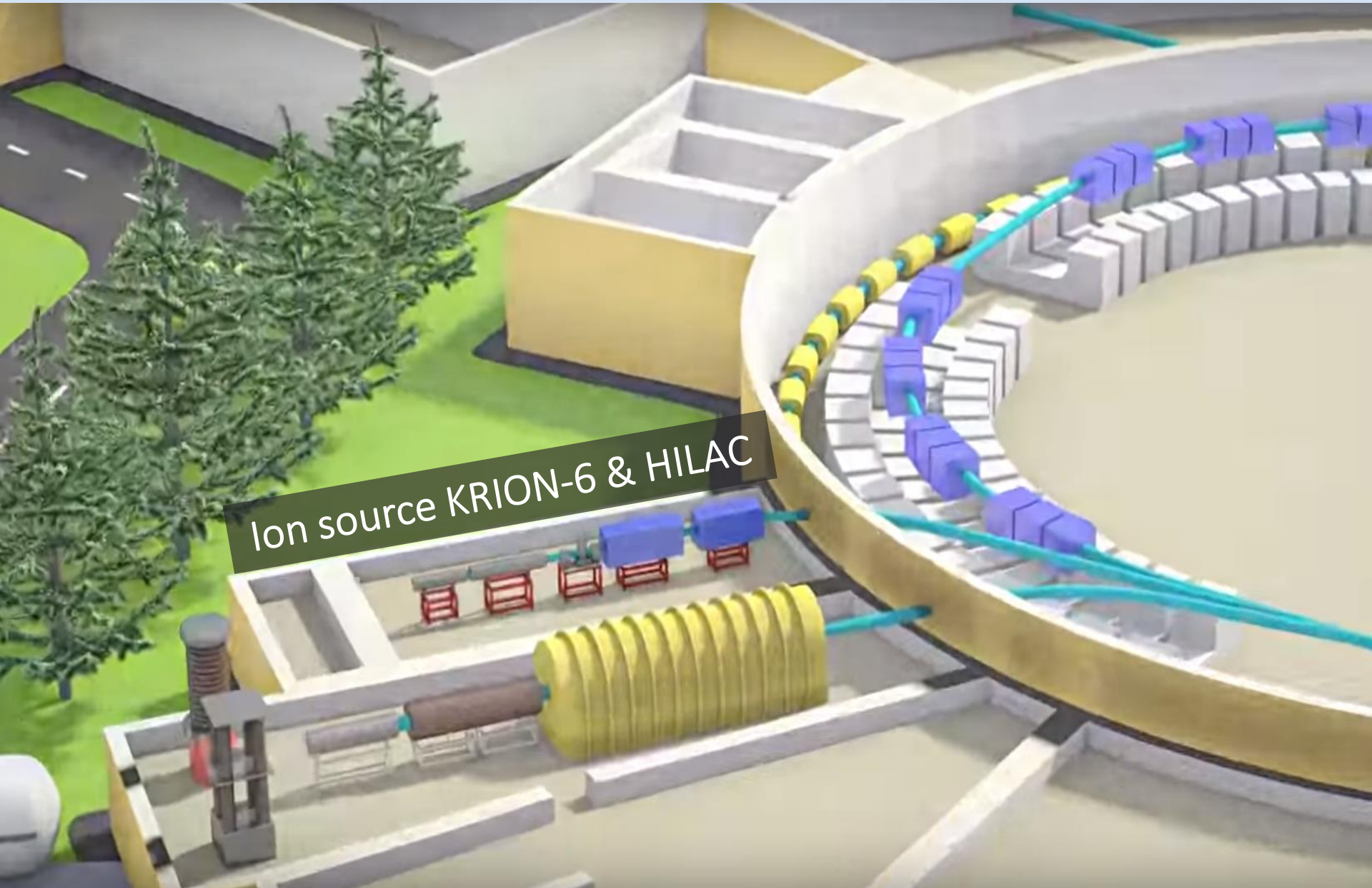
on behalf of the NICA acceleration division

Dubna, 24-28 October 2022

NICA injection complex

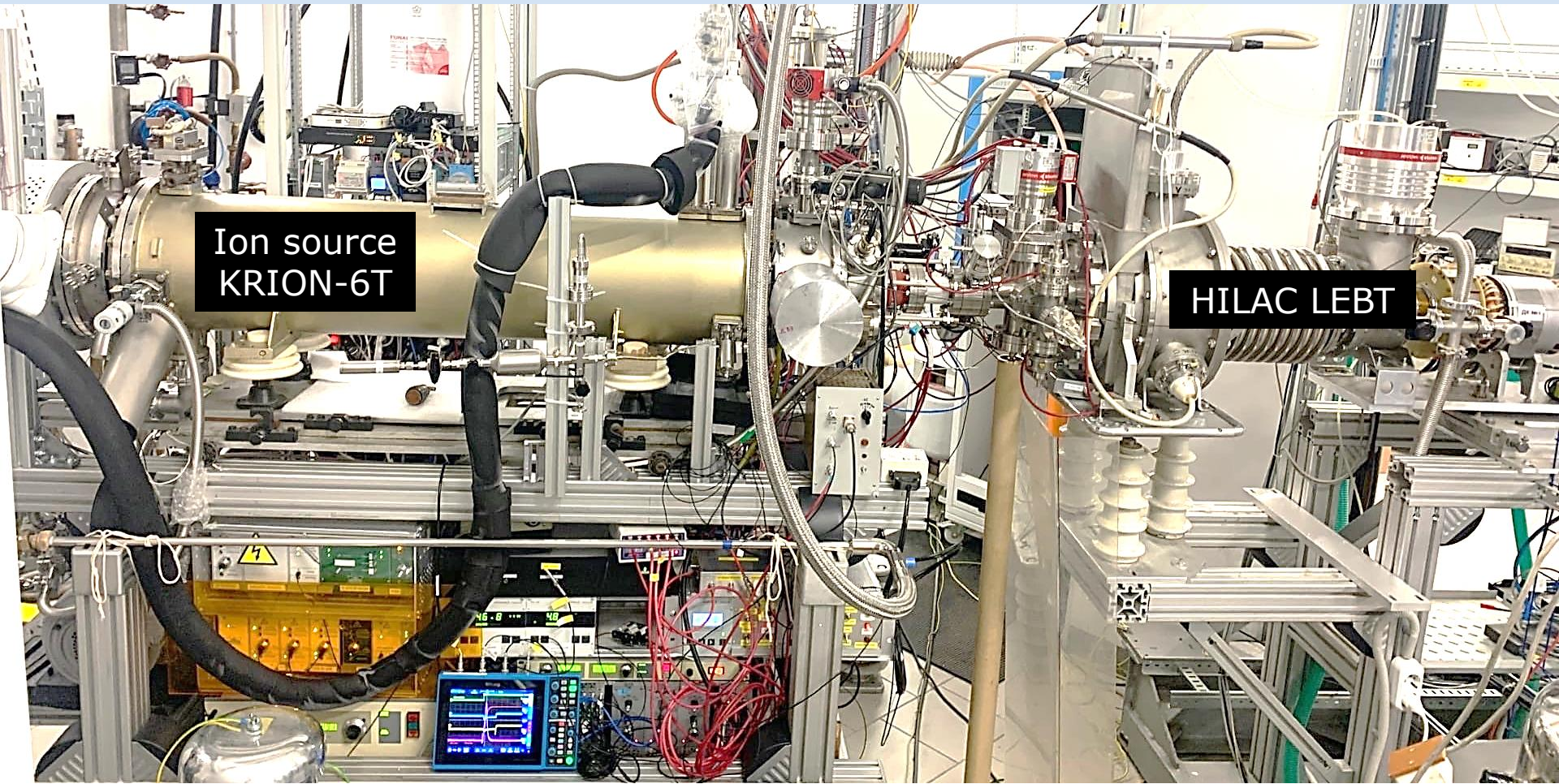


Heavy ion injection



Ion source KRION-6 & HILAC

Heavy ion source KRION 6T



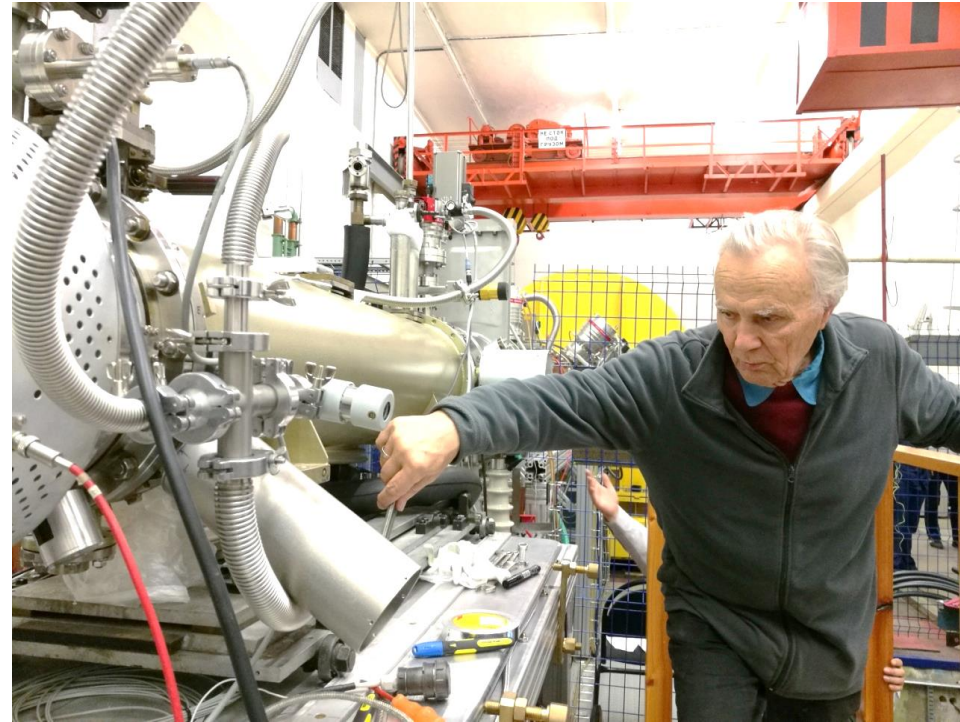
Ions produced and injected: $^{78}\text{Kr}^{17+}$ $^{124}\text{Xe}^{41+}$ $^{40}\text{Ar}^{16+}$ $^{12}\text{C}^{6+}$...

- 5.4 T SC solenoid
- pulsed ion source
- electron string
- cryogenic
- highly charged ions
- unique technology

EBIS = Electron Beam Ion Source

History

- Invented by E.D. Donets at JINR, Dubna in 1968. Au¹⁹⁺ beam in 1969.
- 1970-1985, in Dubna, cryogenic version of EBIS KRION-I,2, bare ions C, N, O, Ne, Ar, Kr, Xe. HCI physics begins.
- 1970-1985, Europe, US, Japan, a lot of EBIS (*EBIS time*), U⁹⁰⁺ !
- 1982, at Bekerley, EBIT, from EBIS, 1990s, SuperEBIT, U⁹²⁺ !
- Since 1985, in accelerator fields, ECRIS time
- 2001-2005, breakthrough of EBIS at JINR, new idea of ESIS, and high current EBIS at BNL.
- In China, Shanghai EBIT

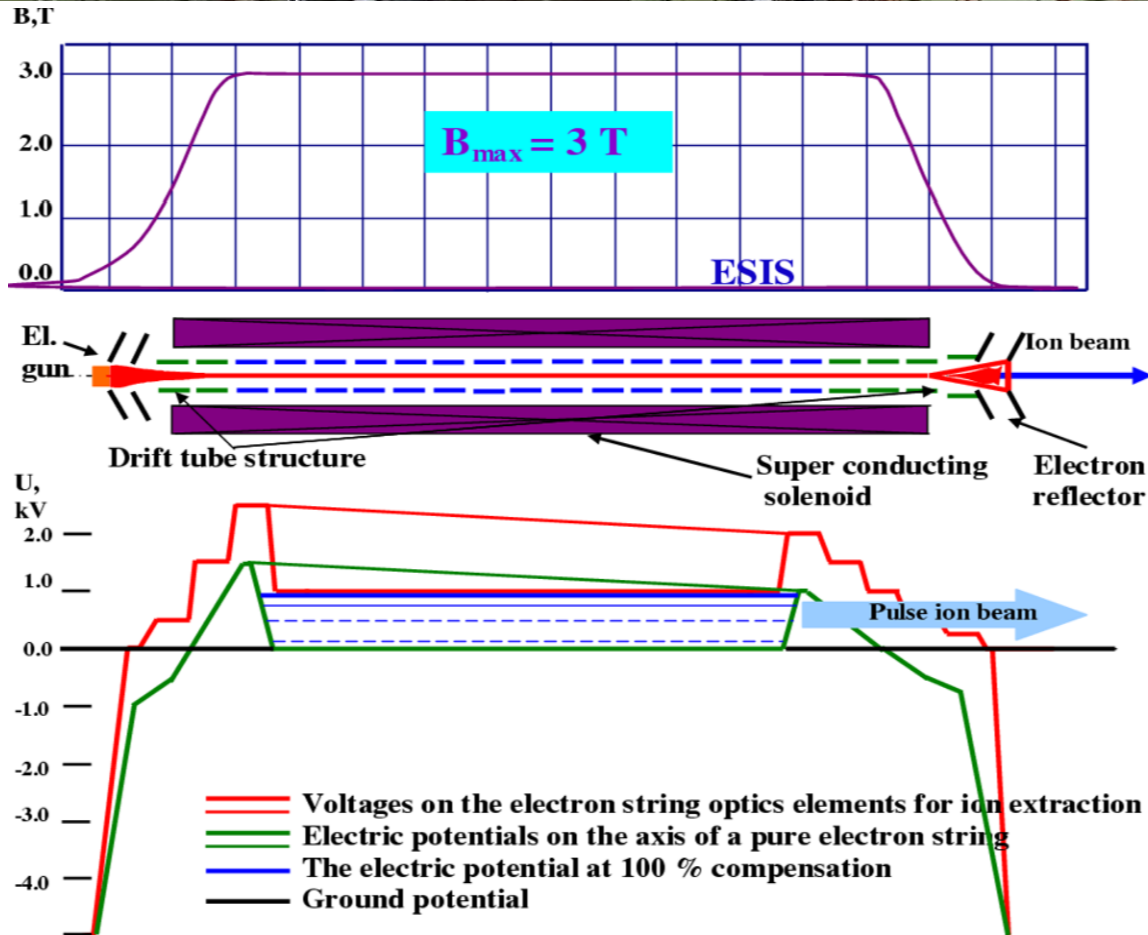


Prof. E.D. Donets near Krion-6T ESIS during Nuclotron run #55, JINR, Dubna, February 2018



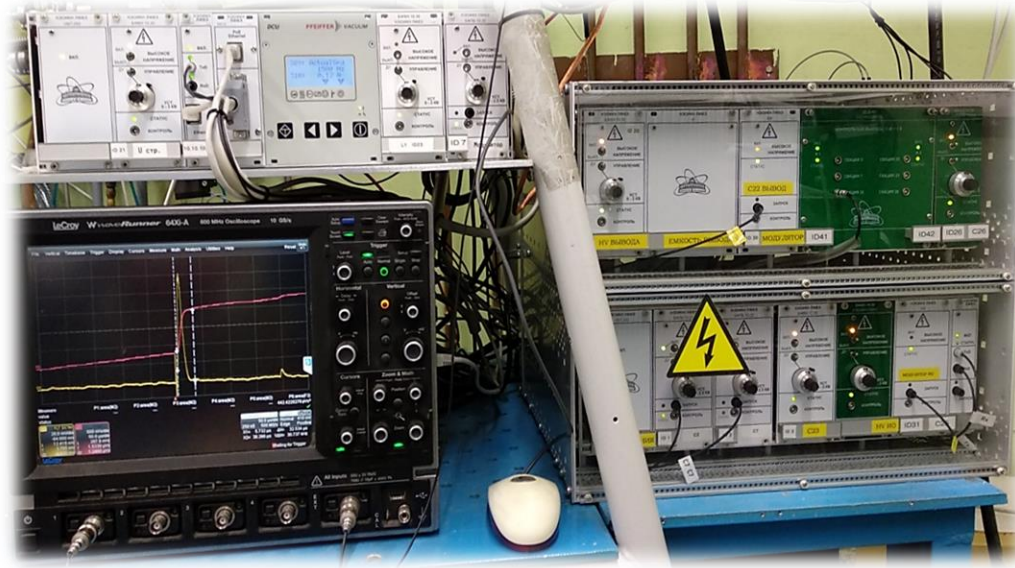
- **ESIS Krion 6T and Krion N1 for NICA JINR**

ESIS = EBIS in electron reflex mode of operation



ESIS KRION 6T electronics

- vacuum
- ion optics supply
- HV electrodes
- **electron gun supply**
- synchronization
- thermometry



Ion motion control system

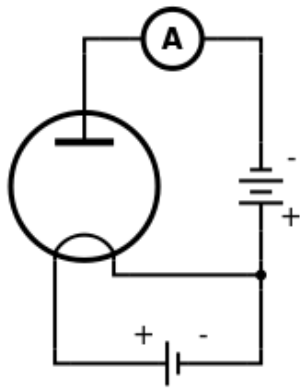
- DC barrier modules
- pulsed barriers modules
- extraction modules
- interface modules
- drift structure divider

Beam diagnostics

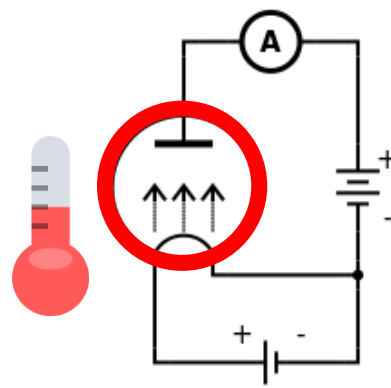
- beam profile monitor
- oscilloscopes
- ion collectors
- ToF system
- induced signals

IrCe cathode

- material IrCe
- emission: thermionic
- small size 1.2 mm
- emission current 6 mA
- heating power AC 1.5V 10A

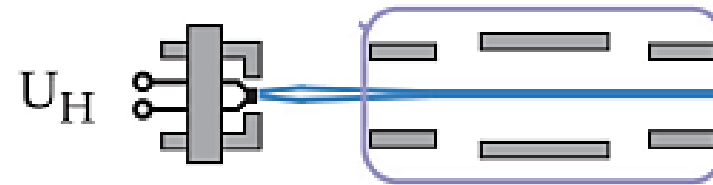


No current



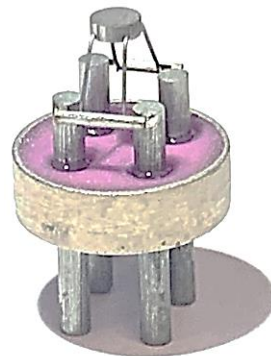
Electron flow

cathode magnet drift tubes

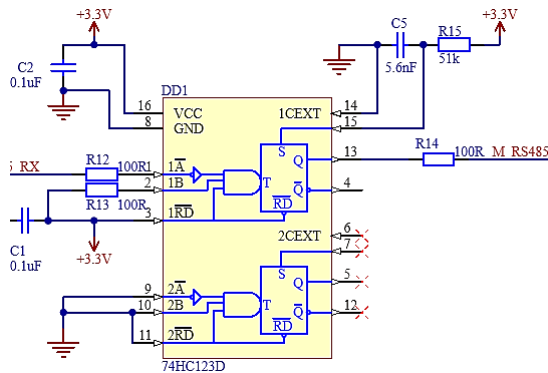
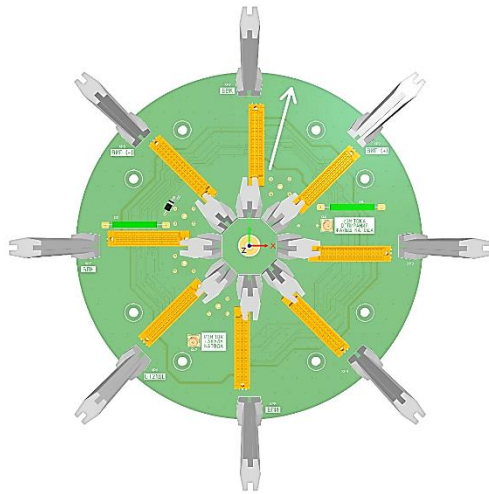
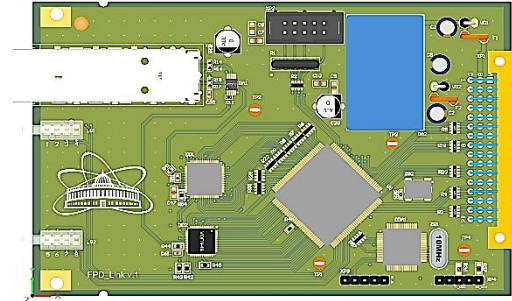
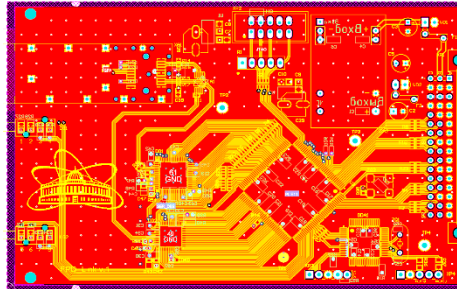
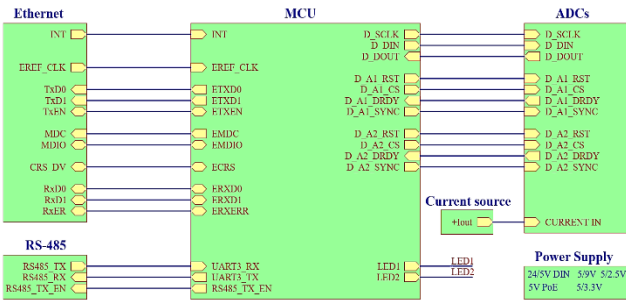




the design process



The design process



```

269
270
271 void task_KORAD(void *pvParameters)
272 {
273     KORAD_params KORADp, KORADtemp;
274     KORAD_state *src_state, src_stateTEMP;
275     unsigned int V2set = 0, I2set = 0;
276     unsigned int State2set = 0;
277
278     while(1)
279     {
280         // set voltage level if queue not empty
281         if(uxQueueMessagesWaiting(KORAD_SetV_q) > 0)
282         {
283             xQueueReceive(KORAD_SetV_q, (void*)&V2set, (TickType_t)0);
284             KORAD_SetVoltage(V2set);
285         }
286
287         // set current value if queue not empty
288         if(uxQueueMessagesWaiting(KORAD_SetI_q) > 0)
289         {
290             xQueueReceive(KORAD_SetI_q, (void*)&I2set, (TickType_t)0);
291             KORAD_SetCurrent(I2set);
292         }
293
294         // set output state if queue not empty
295         if(uxQueueMessagesWaiting(KORAD_SetState_q) > 0)
296         {
297             xQueueReceive(KORAD_SetState_q, &State2set, (TickType_t)0);
298             KORAD_SetState(State2set);
299         }
300
301         // read measured V I, and V I sets
302         KORADp.meas_v = KORAD_GetVoltage();
303         KORADp.set_v = KORAD_GetVSets();
304         KORADp.meas_i = KORAD_GetCurrent();
305         KORADp.set_i = KORAD_GetISets();
306
307         // clear prev measured data if queue is not empty
308         if(uxQueueMessagesWaiting(KORAD_RdParams_q) > 0)
309         {
310             xQueueReceive(KORAD_RdParams_q, &KORADtemp, (TickType_t)0);

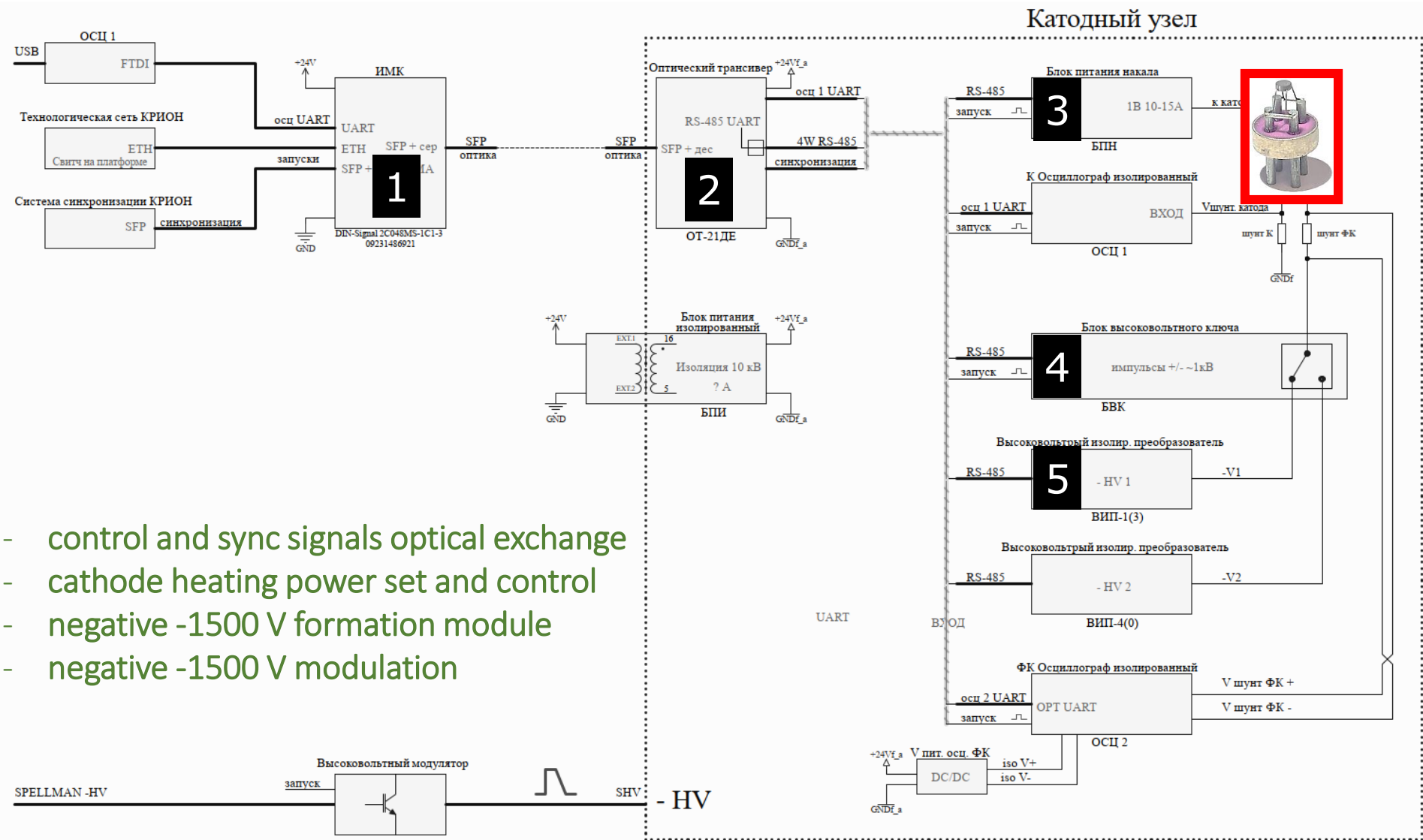
```



Name	Value
U-1.11.2[V]	400
U-1.21.3[V]	398
U-1.31.1[V]	401
P[W]	0
P[W]	571
SW[A]	590
Oil Pressure	.4
Temperature	87
Config	(E) 0x4548
Status	0000 1010 0000 0100

Name	Value
U-1.11.2[V]	401
U-1.21.3[V]	400
U-1.31.1[V]	399
P[W]	0
P[W]	547
SW[A]	571
Oil Pressure	.4
Temperature	91
Config	(AB) 0x4142
Status	1110 1110 0000 1010

Cathode node schematic



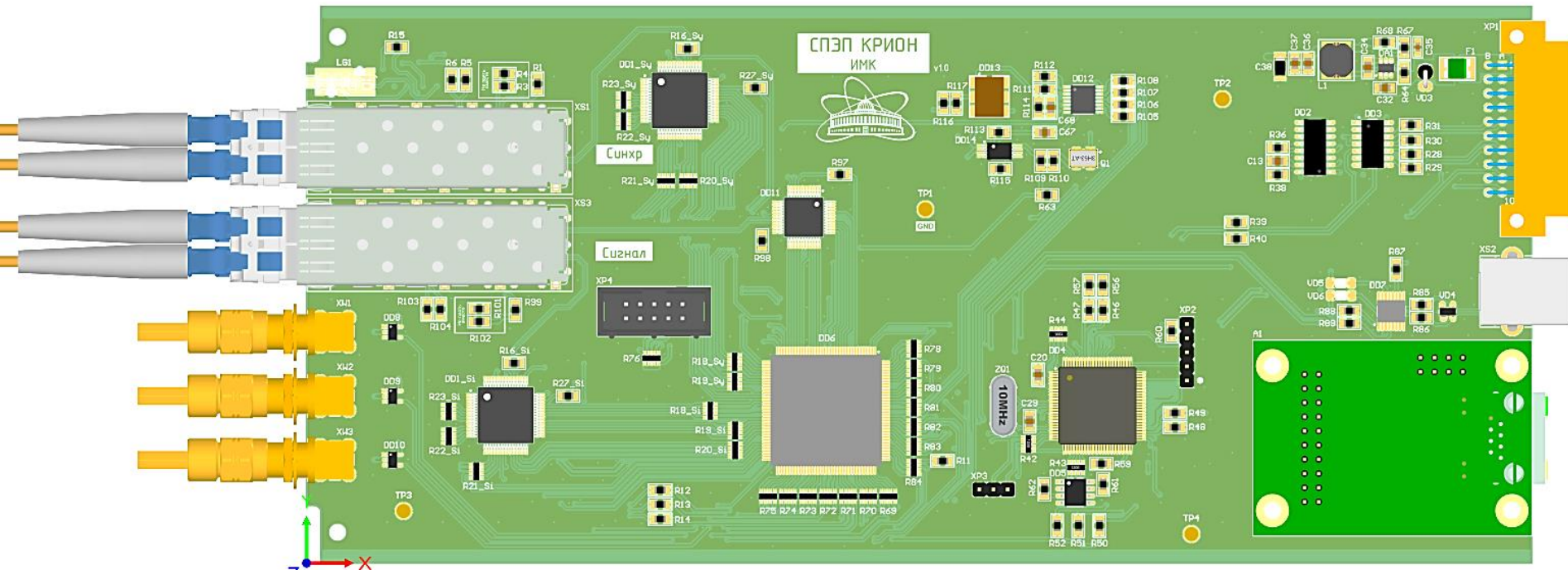
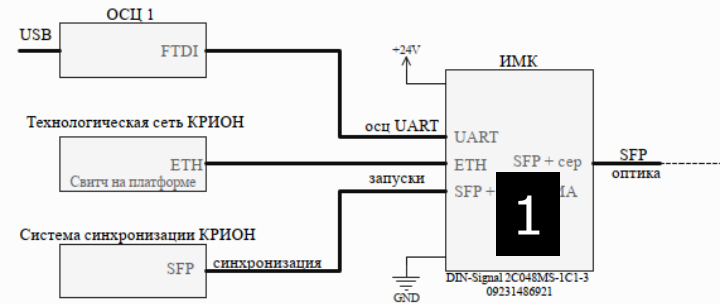
- control and sync signals optical exchange
- cathode heating power set and control
- negative -1500 V formation module
- negative -1500 V modulation

Cathode node => interface module

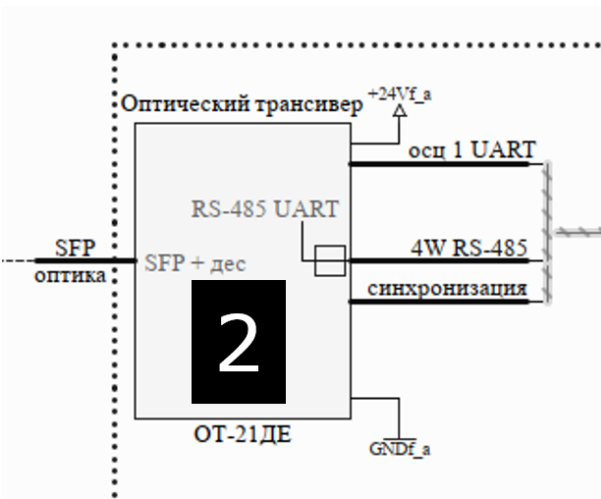
The main idea:

control and sync signals optical exchange

Interfaces: SFP, eth, RS-485, USB



Cathode node => optical isolation module

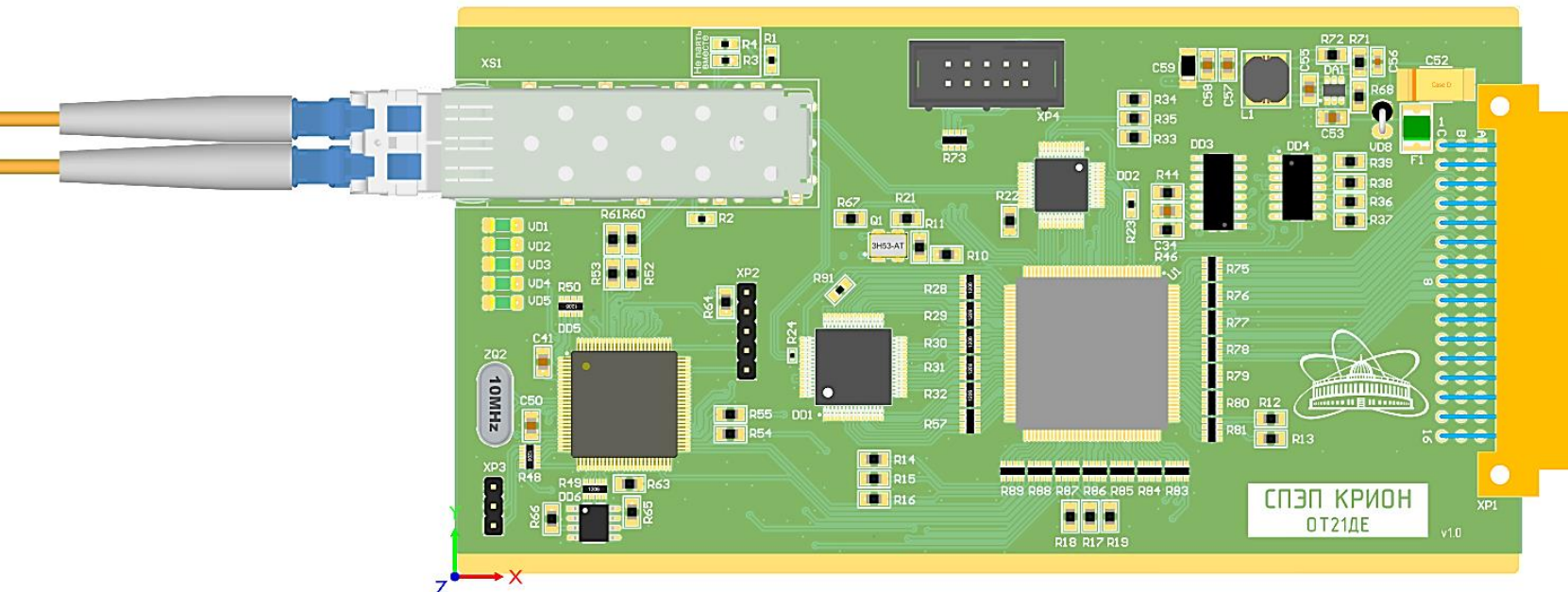


The main idea:

control and sync signals optical exchange

Interfaces:

SFP, RS-485

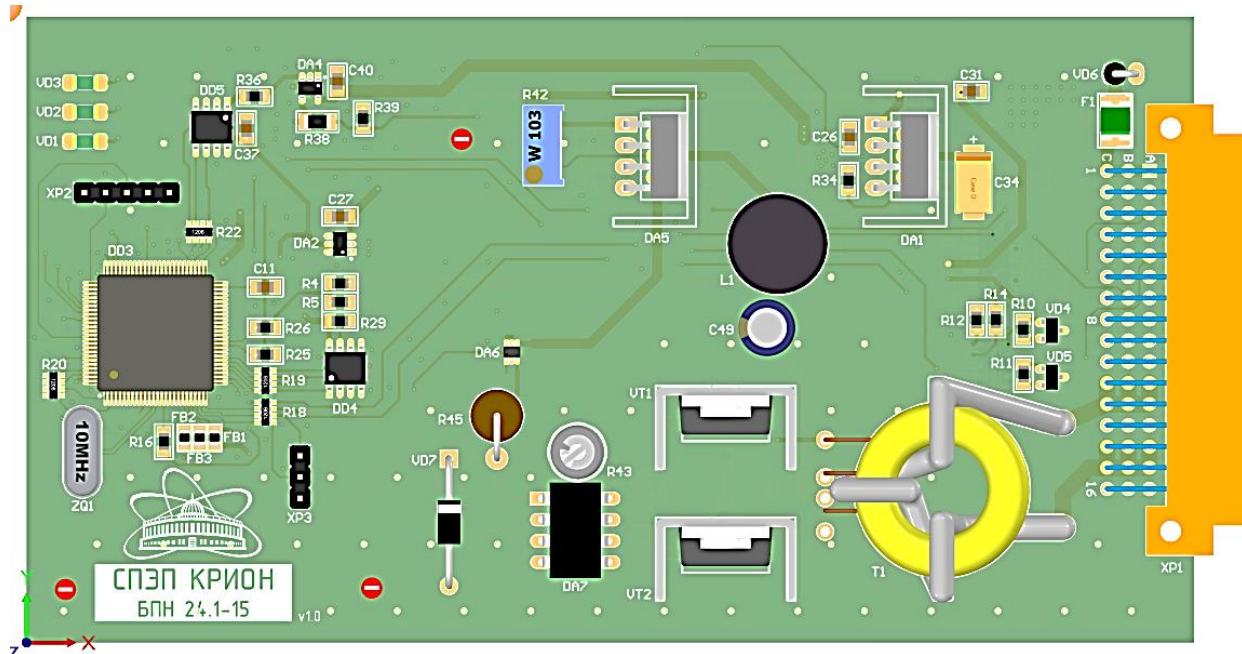


Cathode node => Heating module

The main idea:

cathode heating power set and control

points: 10 kHz sine, 1.5 V, 10 A

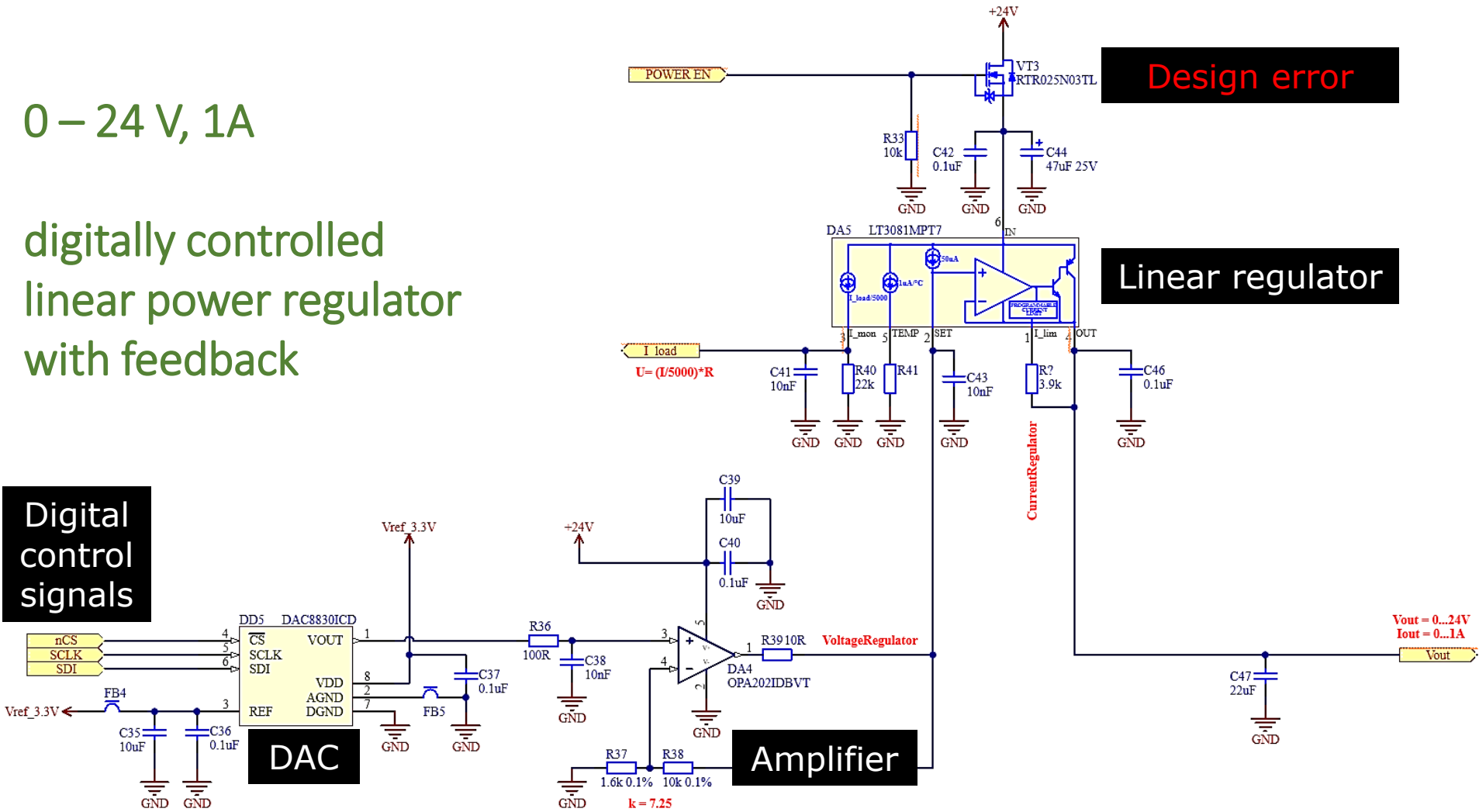


Cathode node => heating module schematic

0 – 24 V, 1A

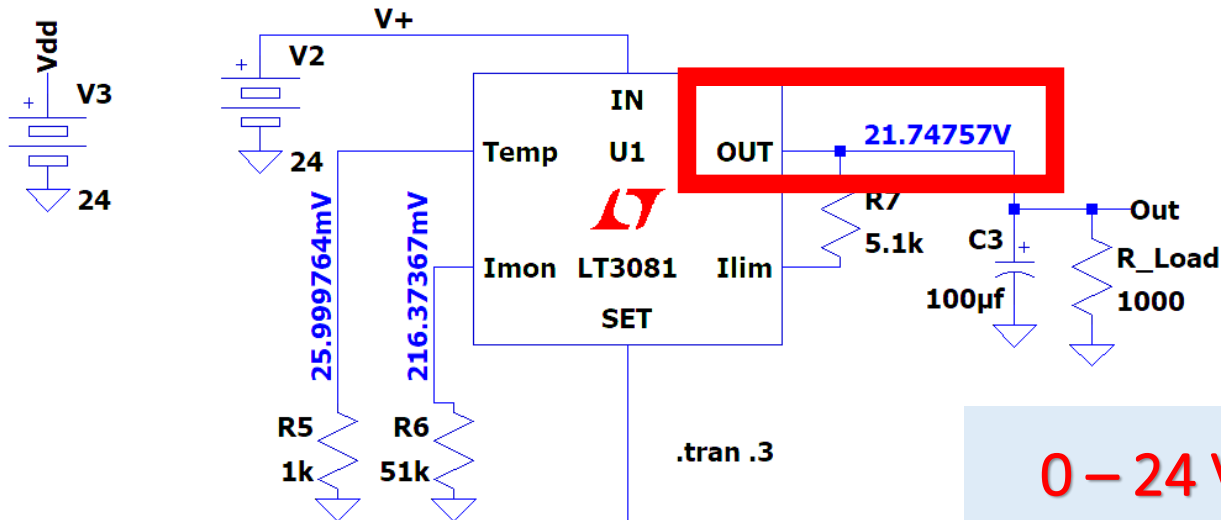
digitally controlled
linear power regulator
with feedback

Digital
control
signals



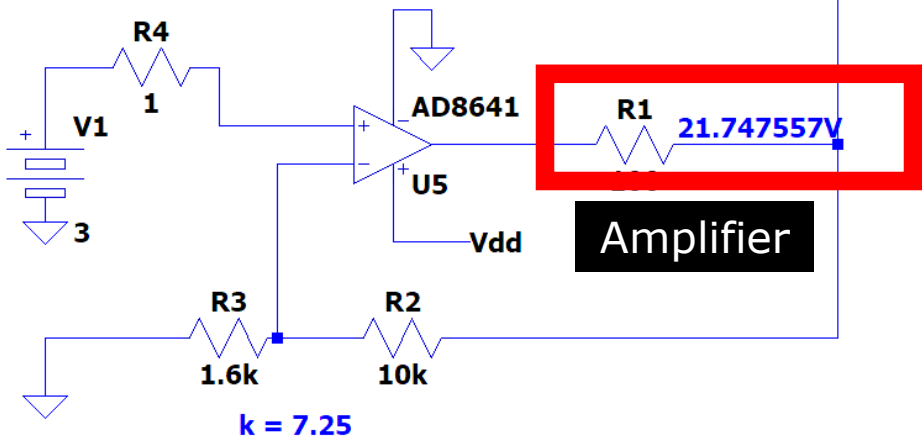


Tricky Linear regulator



0 – 24 V, 1A
P = 24 W

Control voltage
0 – 3.3V
= 0 – 24V



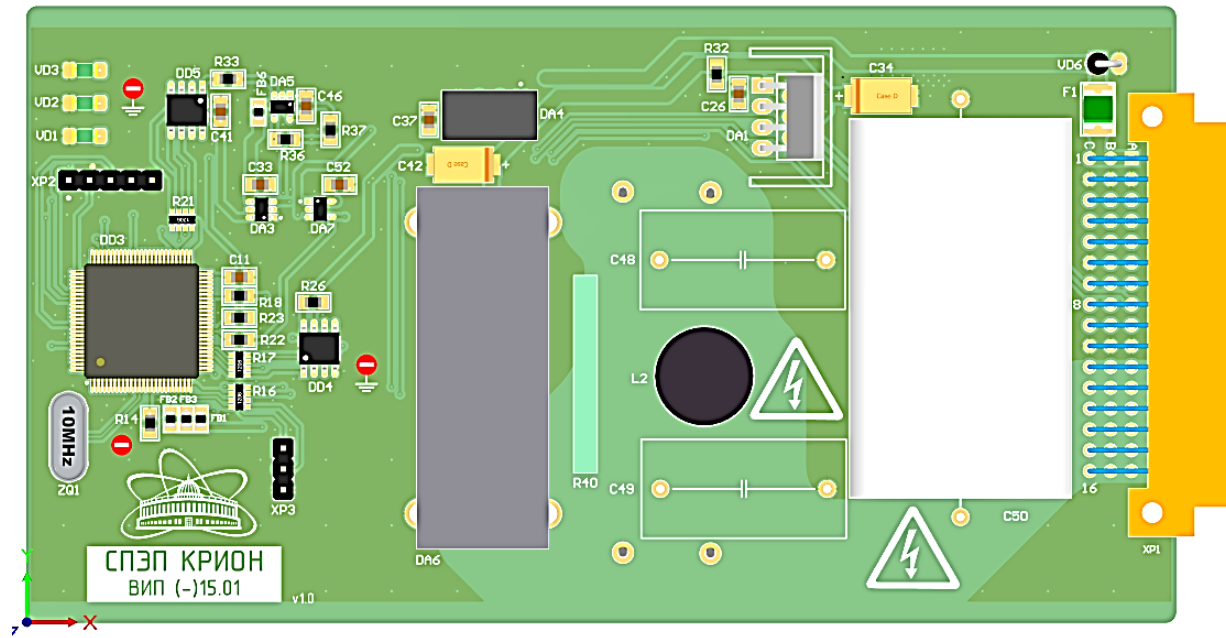
Cathode power:
1.5 V, 10 A
P = 15 W

Cathode node => DC HV module

The main idea:

Negative -1500 V formation module

Interfaces: RS-485, programmable



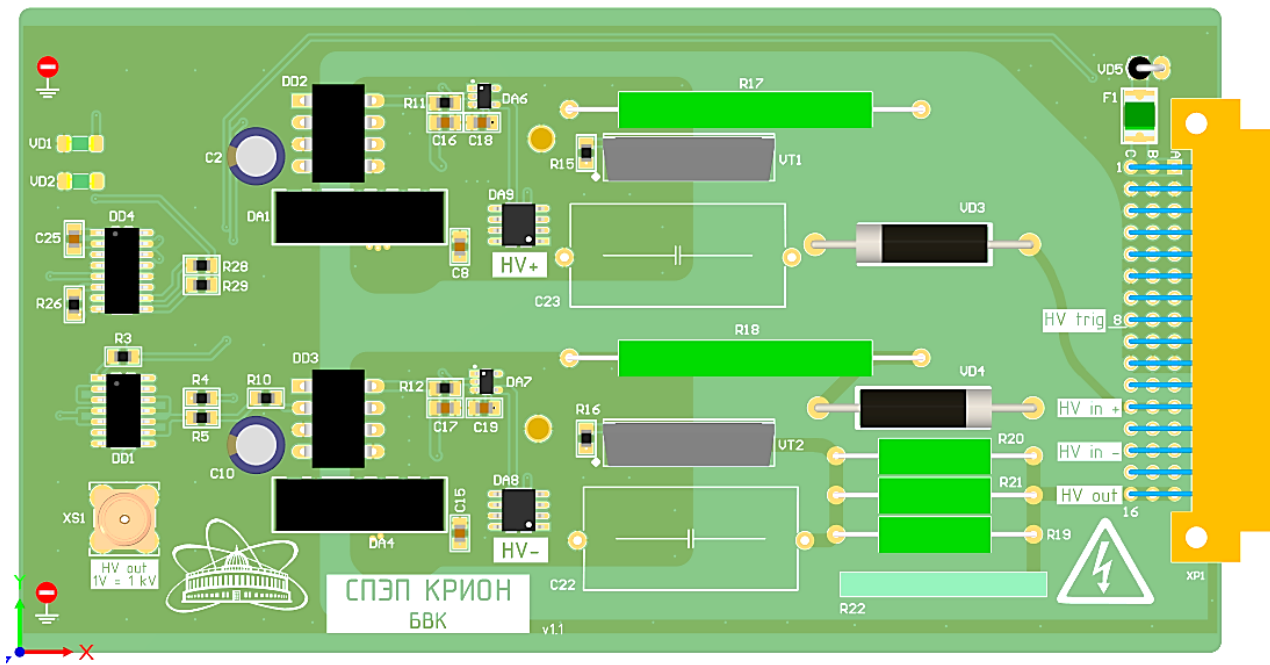
Cathode node => HV modulator



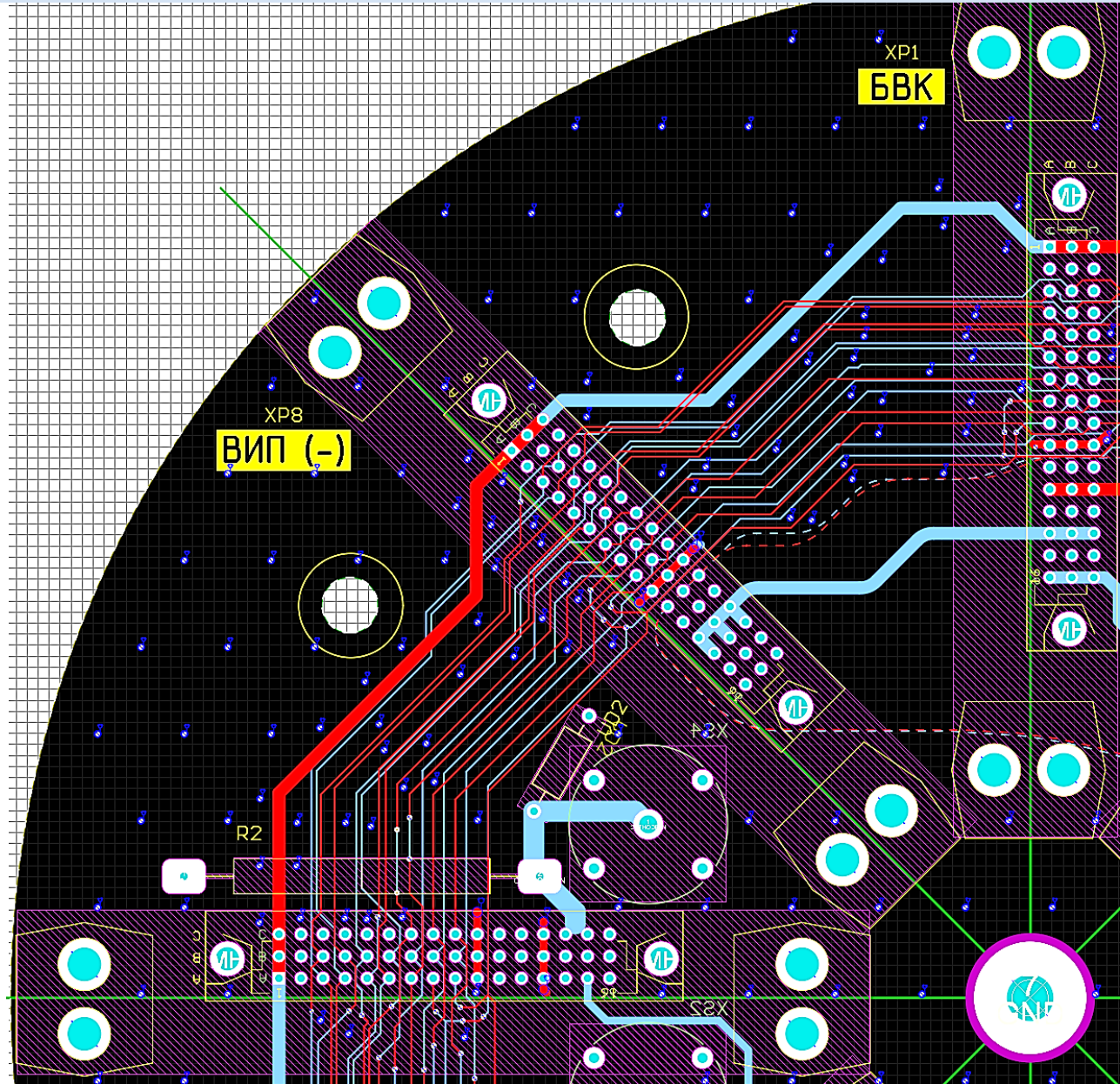
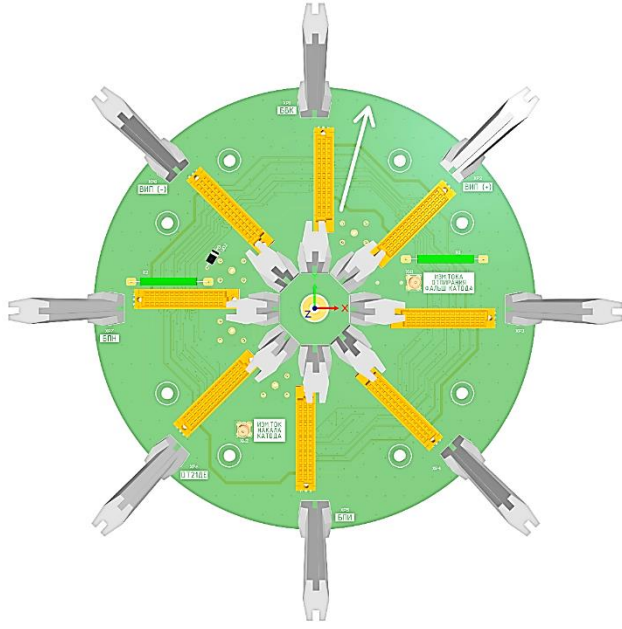
The main idea:

Negative -1500 V modulation module

Interfaces: RS-485, pulsed, IGBT-sw



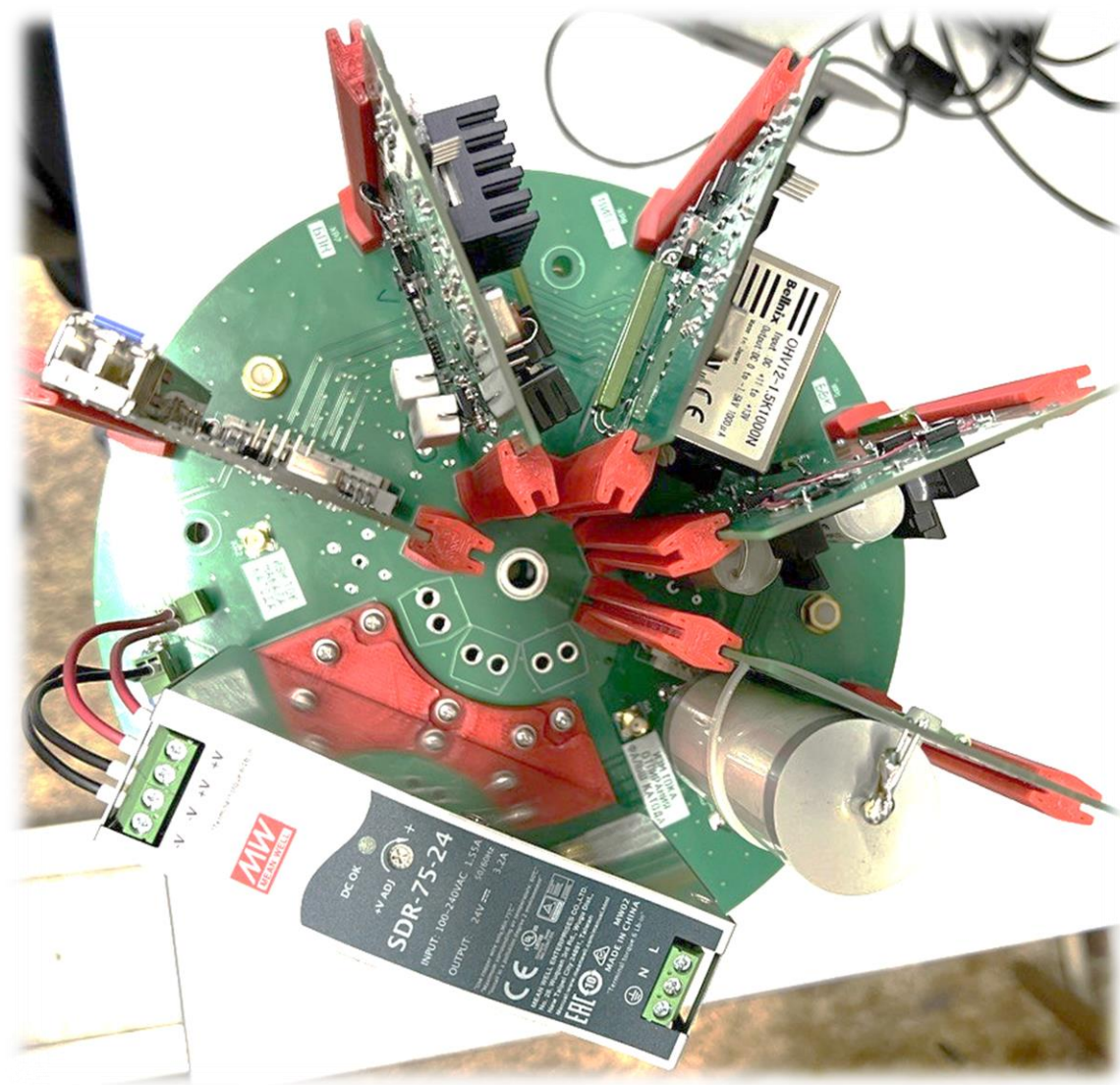
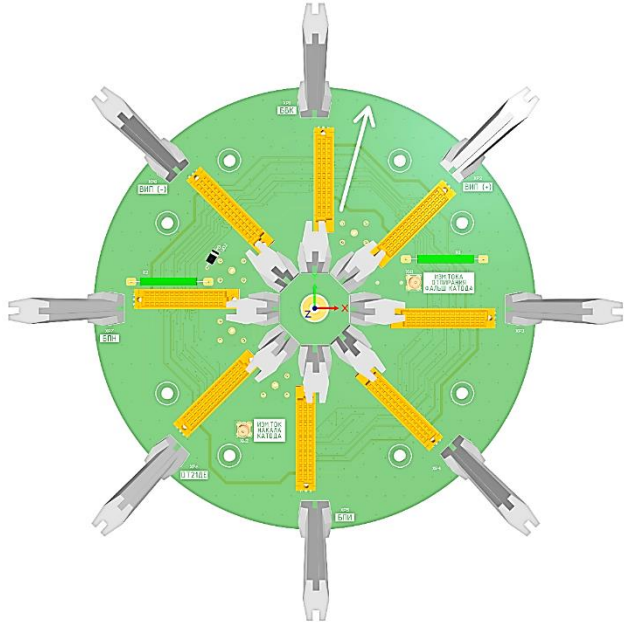
Cathode node => backbone board



ВИП+	
←	Цепь
GND	b1 *
OSC1 UART RX	b2 *
OSC1 UART TX	b3 *
OSC2 UART RX	b4 *
OSC2 UART TX	b5 *
SYNC SIG5	b6 *
SYNC SIG8	b7 *
SYNC SIG11	b8 *
GND	b9 *
HVp	b10 *
	b11 *
	b12 *
	b13 *
	b14 *
	b15 *
	b16 *
	МН
	XP2B

ВИП+	
←	Цепь
GND	c1 *
	c2 *
	c3 *
	c4 *
	c5 *
GND	c6 *
SYNC SIG6	c7 *
SYNC SIG9	c8 *
SYNC SIG12	c9 *
GND	c10 *
	c11 *
	c12 *
	c13 *
	c14 *
	c15 *
	c16 *
	МН
	XP2C

Cathode node => backbone board

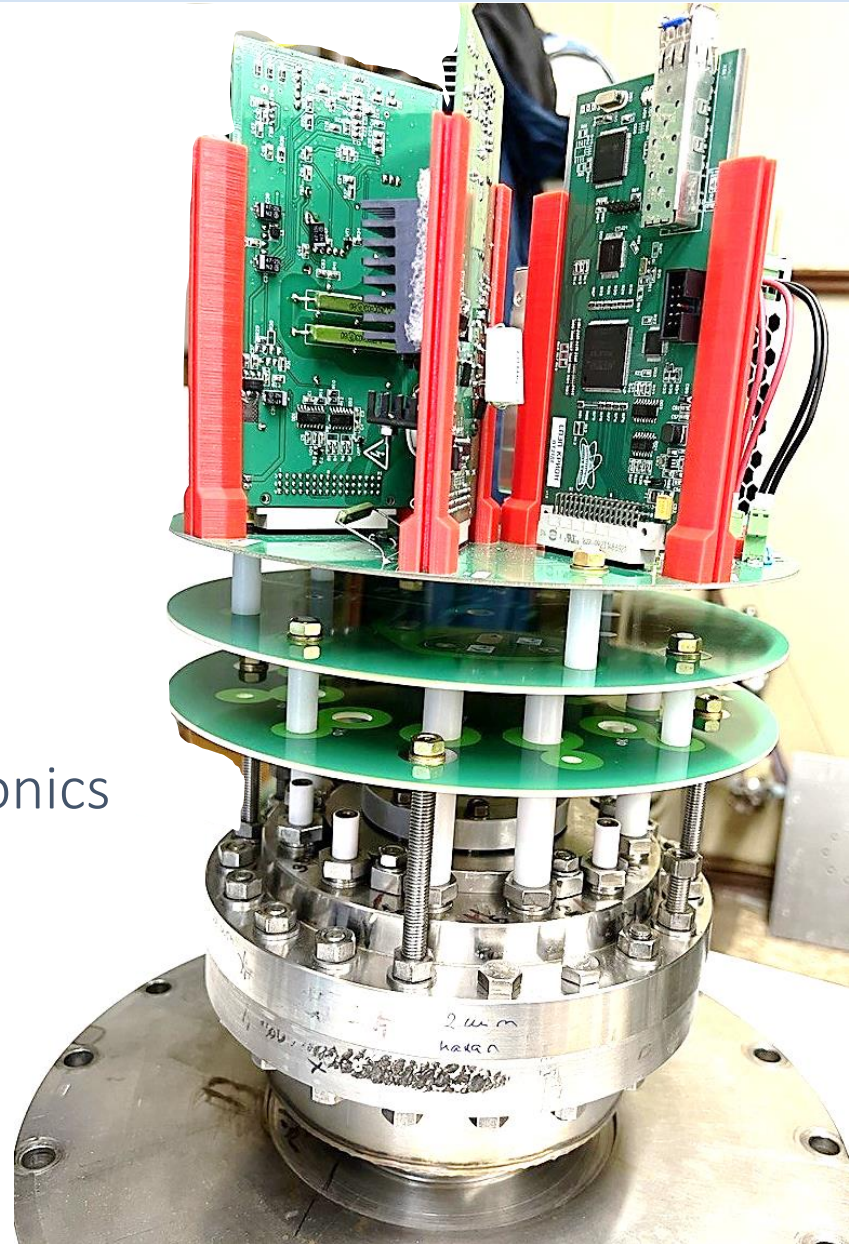
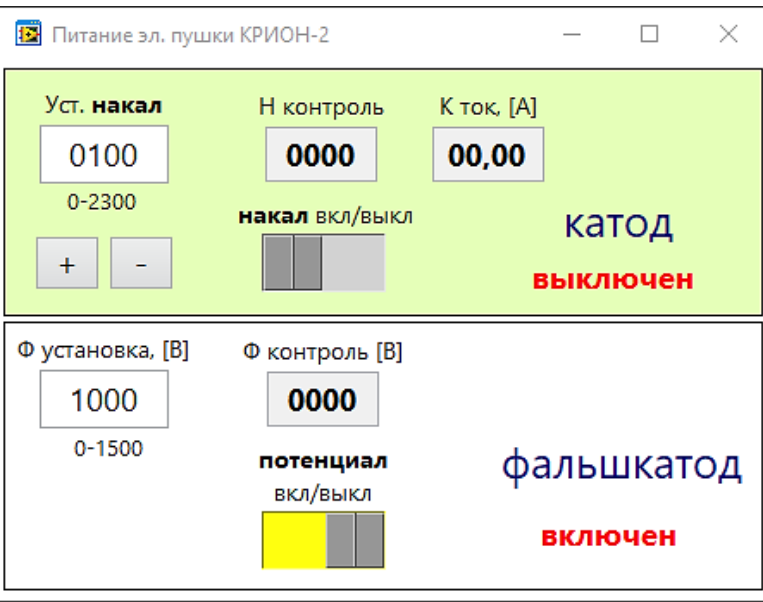


+24V		ВИП+	
		←	Цель
GND	*	b1	*
OSC1 UART RX	*	b2	*
OSC1 UART TX	*	b3	*
OSC2 UART RX	*	b4	*
OSC2 UART TX	*	b5	*
SYNC SIG5	*	b6	*
SYNC SIG8	*	b7	*
SYNC SIG11	*	b8	*
GND	*	b9	*
	*	b10	*
	*	b11	*
	*	b12	*
HVp	*	b13	*
	*	b14	*
	*	b15	*
	*	b16	*
	*	MH	*
	*	XP2B	*

+24V		ВИП+	
		←	Цель
GND	*	c1	*
	*	c2	*
	*	c3	*
	*	c4	*
	*	c5	*
GND	*	c6	*
SYNC SIG6	*	c7	*
SYNC SIG9	*	c8	*
SYNC SIG12	*	c9	*
GND	*	c10	*
	*	c11	*
	*	c12	*
	*	c13	*
	*	c14	*
	*	c15	*
	*	c16	*
	*	MH	*
	*	XP2C	*

Summary

KRION-6T cathode node electronics



The NEW KRION-6T cathode node electronics was designed, produced and tested

At the moment is putting into operation

For technical details – please welcome!



We are ready for collaboration in any technical questions
email: ponkin@jinr.ru

Thank you!

7. KRION-6T on the test bench



Specifications of KRION-6T

Length of the superconducting solenoid	1,2 m
Number of layers	24 layers
Induction	~10 H
Current in the solenoid	90 A (105 A planned)
Field on the axis in the middle (Bmax)	5,4 T (6T planned)
Length of the main ion trap	1 m
Maximum energy of the electrons	10 keV (11,5 keV with trap potential lift)
Emitter material	IrCe
Electron current from the gun	up to 30 mA
Capacity of the ion trap	up to 22 nC

8. Results achieved on the test bench

- the j_T ionization factor is the most important value giving information about the performance of the ESIS
- impossible to measure directly the electron string current, but possible to measure **effective j_T** , using the extracted ions spectrum.

Ion specious	Effective electron string current density j , A/cm ²
Kr ¹⁵⁺	665
Kr ¹⁸⁺	591
Kr ^{24,6+}	847
Xe ^{23,2+}	1090
Xe ^{24,9+}	1579
Xe ^{25,4+}	1587
Tm ^{40,8+}	1092

Examples of number of particles per pulse and times of ionization for different ions

C ⁴⁺	7x10 ⁹	-
Xe ⁴²⁺	5x10 ⁹	350 ms
Xe ³²⁺	-	40 ms
Tm ⁵⁰⁺	3x10 ⁷	-
Au ³³⁺	-	30 ms

The new KRION-6T ion source has much higher effective j (up to 1600 A/cm²) in comparison with the KRION-2 which had only 200 A/cm². Another typical EBIS devices have only 100 - 300 A/cm².